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Transphorm's Automotive GaN FET Wins Award for Innovation and Potential Market Impact

Design News Names the AEC-Q101-qualified Power Semiconductor Winner of the Golden Mousetrap Award

GOLETA, Calif.— March 29, 2018—Transphorm Inc.—the leader in the design and manufacturing of the highest reliability and only qualified high voltage Gallium Nitride (GaN) semiconductors—today announced that its TPH3205WSBQA GaN FET has won the Golden Mousetrap Award for the Electronics & Test: Analog/Power Management/Control category. The GaN FET is the industry's first AEC-Q101-qualified power conversion semiconductor designed to enable power systems within plug-in hybrid electric vehicles (PHEVs) and battery electric vehicles (BEV). Transphorm's technology was recognized officially during a formal ceremony hosted by Design News in February.

The Golden Mousetrap Awards acknowledge and recognize people, companies, and technologies who are driving innovation in design, engineering, and manufacturing. Design News' editors looked at hundreds of innovation-leading submissions to come up with the best in level of innovation, benefits to user, and market differentiation.

Transphorm first announced the TPH3205WSBQA GaN FET in March 2017 at the Applied Power Electronics Conference (APEC). The device is the first of its kind to successfully pass the Automotive Electronics Council's AEC-Q101 stress tests for automotive-grade discrete semiconductors. In turn, automotive power system manufacturers gain access to the breakthrough power conversion technology (GaN) via a product that is tested for and proven to provide robustness, quality, reliability, and performance.

Transphorm's automotive GaN FET targets on-board chargers (OBC), DC to AC inverters, and DC to DC systems such as air conditioning, heating, oil pumps, dynamic suspension, and power steering to name a few. Aside from the beneficial inherent bidirectional nature of GaN versus the unidirectional nature of Silicon, Transphorm's GaN platform offers increased power efficiency (greater than 99 percent), up to a 40 percent increase in power density, lighter system weight, and a reduction of overall system cost.

Welcome to the GaN Revolution!
Transphorm designs and manufactures the highest performance, highest reliability GaN semiconductors for high-voltage power conversion applications. Holding one of the largest IP portfolios (600+ patents), Transphorm produces the industry's only JEDEC and AEC-Q101 qualified GaN FET. This is due to a vertically-integrated business approach, which allows for innovation at every development stage: design, fabrication, device, and application support. Transphorm: moving power electronics beyond Silicon limits. Website: transphormusa.com Twitter: @transphormusa

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